

MSKSEMI 美森科

SEMICONDUCTOR



ESD



TVS



TSS



MOV



GDT



PLED

TL431BSxx-xx-MS

Product specification

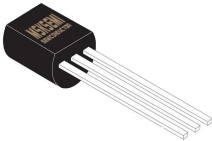
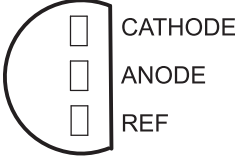
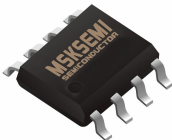
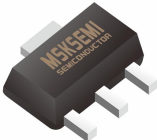
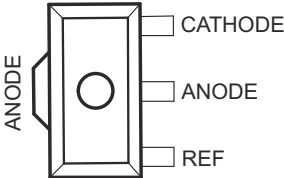
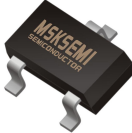
DESCRIPTION

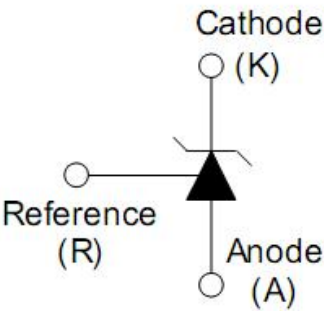
The TL431BSxx-xx-MS is a three-terminal adjustable regulator series with a guaranteed thermal stability over applicable temperature ranges. The output voltage may be set to any value between Vref (approximately 2.5 volts) and 40 volts with two external resistors. These devices have a typical dynamic output impedance of 0.2Ω. Active output circuitry provides a very sharp turn-on characteristic, making these devices excellent replacement for zener diodes in many applications.

FEATURES

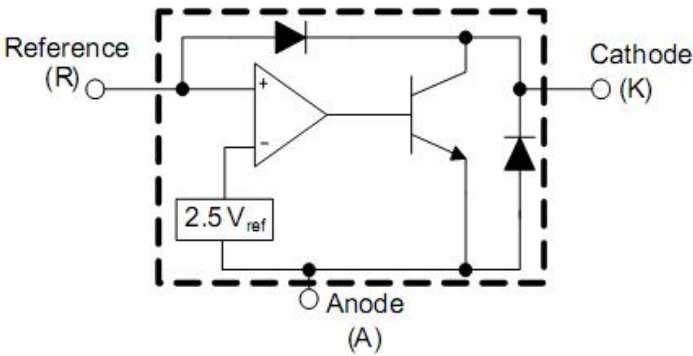
- Programmable Output Voltage to 36V
 - Low Dynamic Output Impedance 0.27Ω (Typ)
 - Sink Current Capability of 0.1 mA to 100 mA
 - Equivalent Full-Range Temperature Coefficient of 50 ppm/°C
- Temperature Compensated for Operation over Full Rated Operating Temperature Range
 - Low Output Noise Voltage
 - Fast Turn on Respons
 - TO-92, SOP-8, SOT-89-3 or SOT-23 packages

Reference News

TO-92	PIN CONFIGURATION	MARKING
		
SOP-8	PIN CONFIGURATION	MARKING
	CATHODE ANODE ANODE NC 1 2 3 4 8 7 6 5 REF ANODE ANODE NC NC – No internal connection	
SOT-89-3	PIN CONFIGURATION	MARKING
		
SOT-23	PIN CONFIGURATION	MARKING
	CATHODE REF 1 2 3 ANODE	



Symbol



Representative Block diagram

ORDER INFORMATION

P/N	PKG	QTY
TL431BSO-7MS	TO-92	1000
TL431BSA-7-MS	SOT-23	3000
TL431BST-7-MS	SOT89-3	1000
TL431BS-13-MS	SOP-8	2500

ABSOLUTE MAXIMUM RATINGS

(Operating temperature range applies unless otherwise specified)

Characteristic	Symbol	Value	Unit
Cathode Voltage	V_{KA}	36	V
Cathode Current Range (Continuous)	I_K	-100 ~ 150	mA
Reference Input Current Range	I_{REF}	-0.05 ~ +10	mA
Power Dissipation at 25°C: TO – 92 Package ($R_{\theta JA} = 178^{\circ}C/W$) SOT – 23 – 3 Package ($R_{\theta JA} = 625^{\circ}C/W$)	P_D	0.7 0.2	W W
Junction Temperature Range	T_J	-40 ~ 125	°C
Storage Temperature Range	T_{stg}	-65 ~ +150	°C

RECOMMENDED OPERATING CONDITIONS

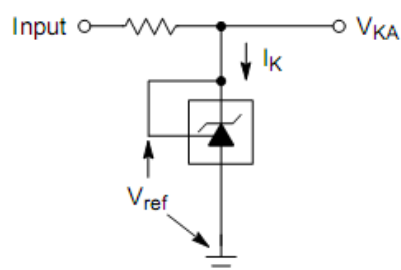
Characteristic	Symbol	Test Condition	Min	Typ	Max	Unit
Cathode Voltage	V_{KA}		V_{REF}		36	V
Cathode Current	I_K		0.5		100	mA

ELECTRICAL CHARACTERISTICS

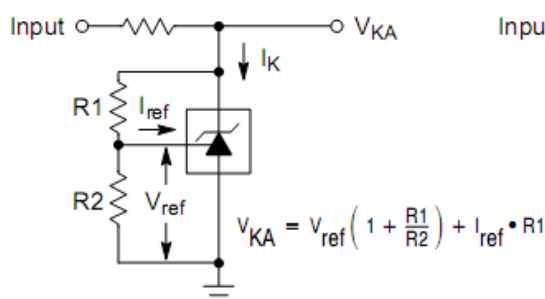
($T_a = 25^\circ\text{C}$, $V_{KA} = V_{REF}$, $I_K = 10\text{mA}$ unless otherwise specified)

Characteristic	Symbol	Test Condition	Min	Typ	Max	Unit
Reference Input Voltage	V_{REF}	$V_{KA} = V_{REF}$, $I_K = 10\text{mA}$	2.483	2.495	2.507	V
Deviation of Reference Input Voltage Over Full Temperature Range	$V_{REF(\text{dev})}$	$T_{\min} \leq T_a \leq T_{\max}$		3	17	mV
Ratio of Change in Reference Input Voltage to the Change in Cathode Voltage	$\Delta V_{REF}/\Delta V_{KA}$	$\Delta V_{KA} = 10\text{V} - V_{REF}$ $\Delta V_{KA} = 36\text{V} - 10\text{V}$	-0.4 -0.4	0.0 0.0	2.7 2.0	mV/V
Reference Input Current	I_{REF}	$R_1 = 10\text{K}\Omega$, $R_2 = \infty$		1.8	4	μA
Deviation of Reference Input Current Over Full Temperature Range	$I_{REF(\text{dev})}$	$R_1 = 10\text{K}\Omega$, $R_2 = \infty$		0.4	1.2	μA
Minimum Cathode Current for Regulation	$I_{K(\min)}$			0.25	0.5	mA
Off-State Cathode Current	$I_{K(\text{off})}$	$V_{KA} = 40\text{V}$, $V_{REF} = 0$		0.17	0.9	μA
Dynamic Impedance	Z_{KA}	$I_K = 1\text{mA}$ 100 mA, $f \leq 1.0\text{KHz}$		0.27	0.5	Ω

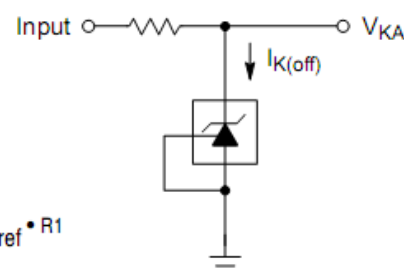
TEST CIRCUITS



Test Circuit
for $V_{KA} = V_{ref}$

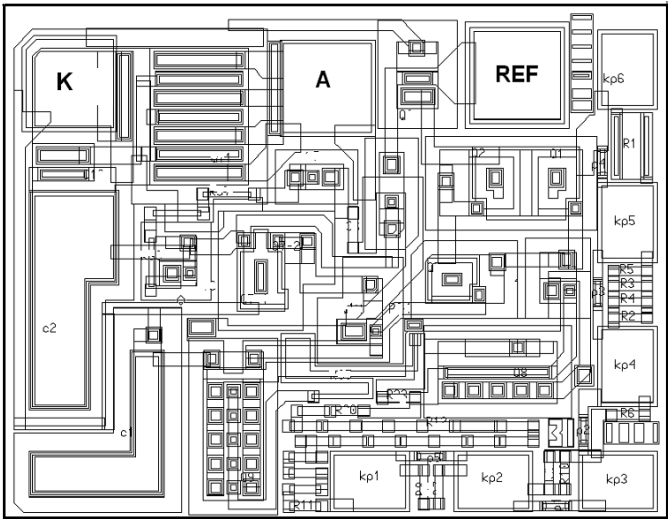


Test Circuit
for $V_{KA} > V_{ref}$



Test Circuit
for $I_{K(\text{off})}$

PAD LAYOUT



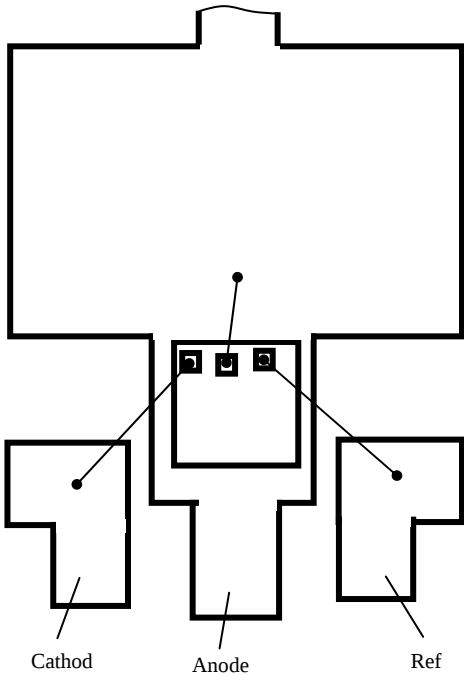
PHISICAL CHARACTERISTICS:

- Wafer Diameter.....100 ± 0.5mm
- Wafer Thickness..... 260 ±20 μm
- Die size.....0.76 x 0.60 mm²
- Scribe Width.....60 μm
- Pad Size86 x 86 μm
- Passivation.....PECVD
- Backside metallizationwithout metallization

PAD LOCATION

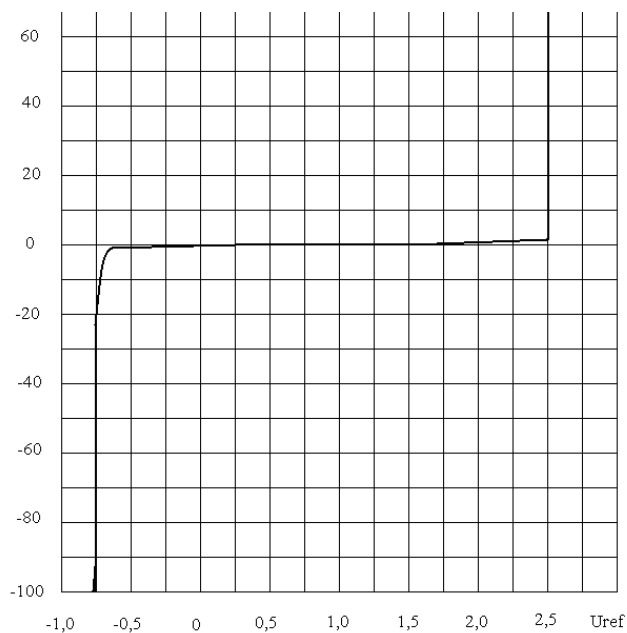
Pad Name	Description	X	Y
K	Cathode	56	445
A	Anode	328	440
R	Reference	528	453

BONDING DIAGRAM

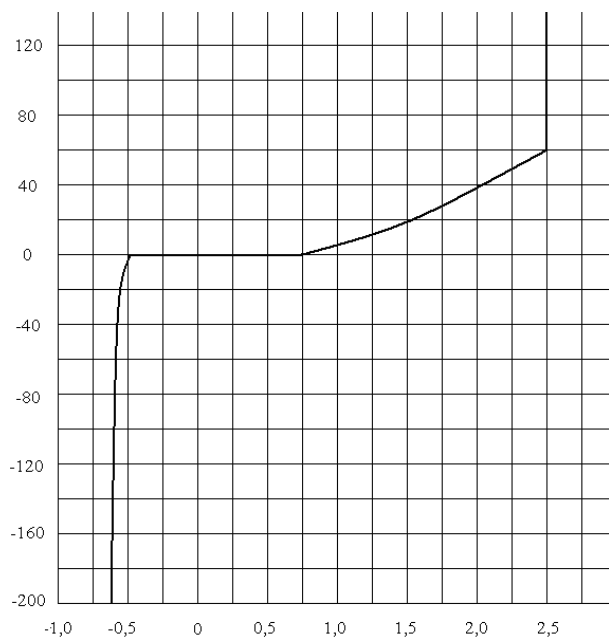


TYPICAL PERFORMANCE CHARACTERISTICS

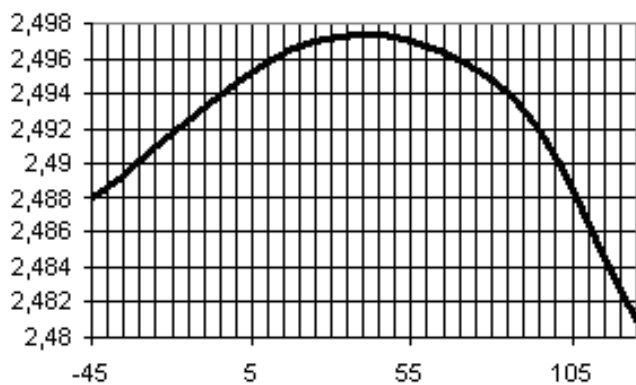
**Cathode Current I_k (mA)
vs. Cathode Voltage U_k (V)**



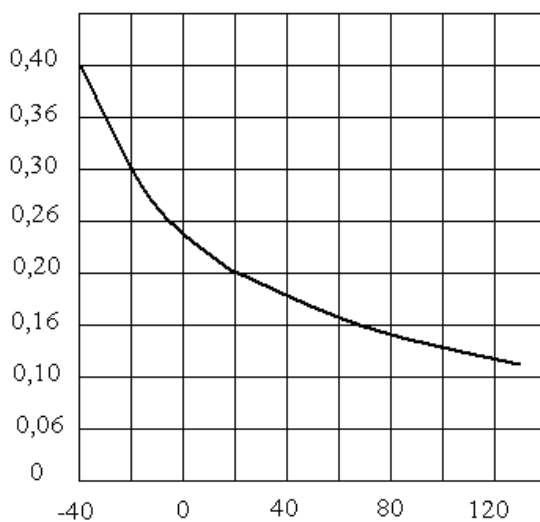
**Cathode Current I_k (μA)
vs. Cathode Voltage U_k (V)**



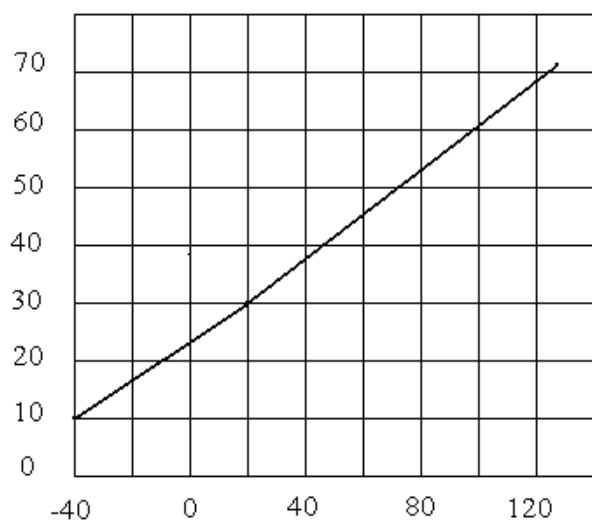
**Reference Voltage U_{ref} (V)
vs. Junction Temperature T_j (°C)
 $I_k=10\text{mA}$**



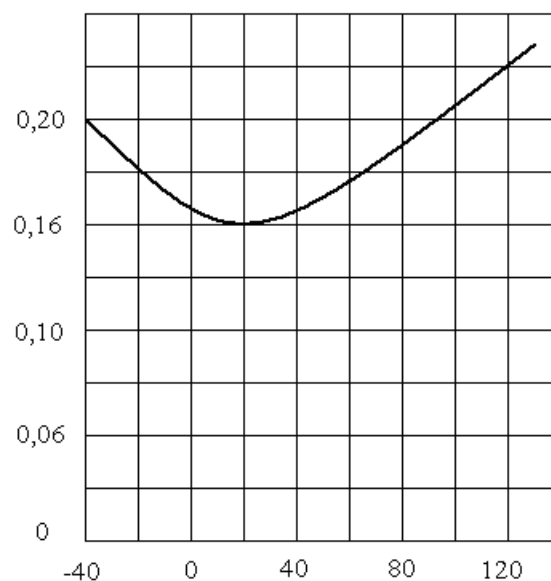
**Reference Input Current I_{ref} (μA)
vs. Junction Temperature T_j (°C)
 $I_k=10\text{mA}$**



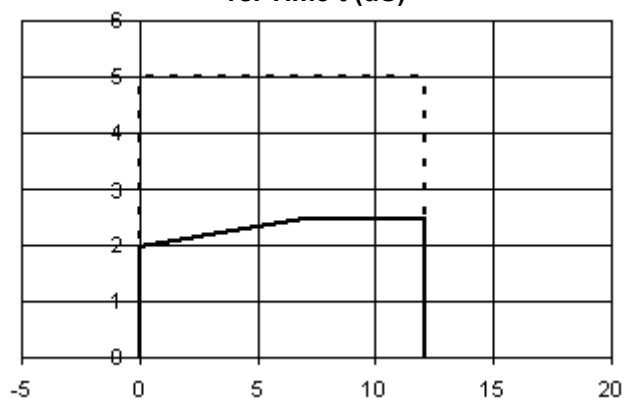
Off-State Cathode Current I_{koff} (μA)
 vs. Junction Temperature T_j ($^{\circ}C$)
 $U_{ka}=36V$



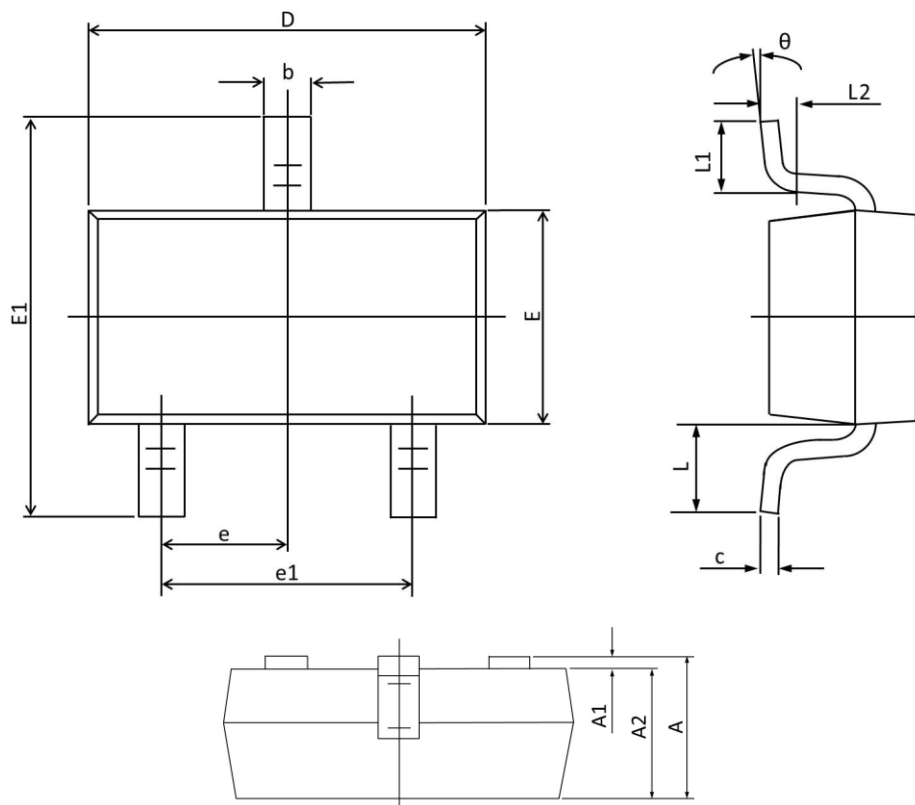
Dynamic Impedance Z_{ka} (Ohm)
 vs. Junction Temperature T_j ($^{\circ}C$)
 $I_k = 1 \div 100$ mA



Pulse Response Input and Output Voltage (V)
 vs. Time t (μs)

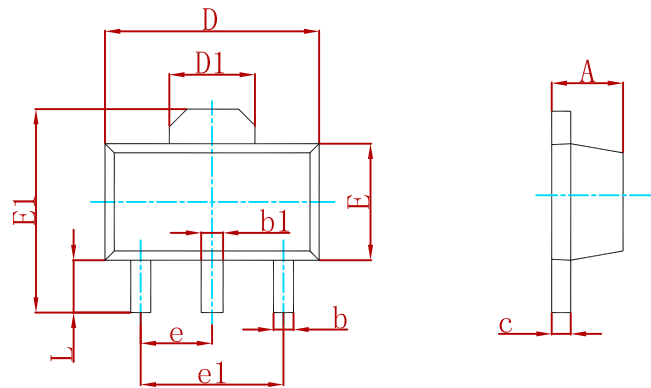


SOT-23 PACKAGE INFORMATION



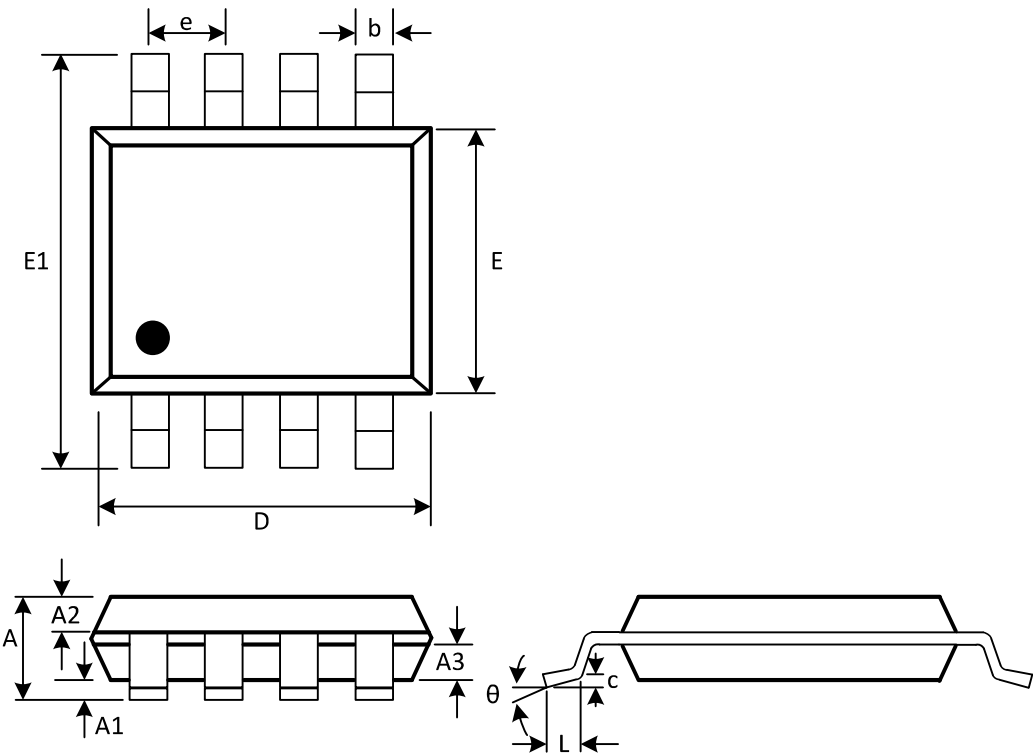
Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Max	Min	Max	Min
A	1.150	0.900	0.045	0.035
A1	0.100	0.000	0.004	0.000
A2	1.050	0.900	0.041	0.035
b	0.500	0.300	0.020	0.012
c	0.150	0.080	0.006	0.003
D	3.000	2.800	0.118	0.110
E	1.400	1.200	0.055	0.047
E1	2.550	2.250	0.100	0.089
e	0.95 TYP.		0.037 TYP.	
e1	2.000	1.800	0.079	0.071
L	0.55 REF.		0.022 REF.	
L1	0.500	0.300	0.020	0.012
L2	0.25 TYP.		0.01 TYP.	
θ	8°	0°	8°	0°

SOT-89 PACKAGE MECHANICAL DATA



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	1.400	1.600	0.055	0.063
b	0.320	0.520	0.013	0.020
b1	0.400	0.580	0.016	0.023
c	0.350	0.440	0.014	0.017
D	4.400	4.600	0.173	0.181
D1	1.550 REF.		0.061 REF.	
E	2.300	2.600	0.091	0.102
E1	3.940	4.250	0.155	0.167
e	1.500 TYP.		0.060 TYP.	
e1	3.000 TYP.		0.118 TYP.	
L	0.900	1.200	0.035	0.047

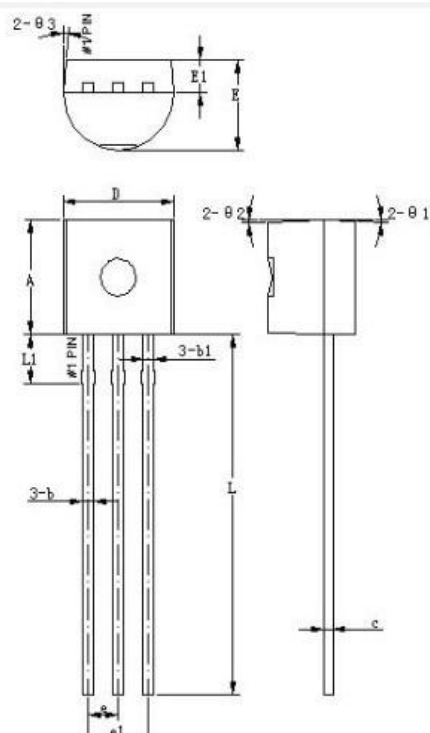
SOP-8 PACKAGE MECHANICAL DATA



(Unit: mm)

Symbol	Min	Max
A	1.300	1.600
A1	0.050	0.200
A2	0.550	0.650
A3	0.550	0.650
b	0.356	0.456
c	0.203	0.233
D	4.800	5.000
e	1.270(BSC)	
E	3.800	4.000
E1	5.800	6.200
L	0.400	0.800
θ	0°	8°

TO-92 PACKAGE MECHANICAL DATA



符号	机械尺寸/mm		
	最小值	典型值	最大值
A	4.5	4.6	4.7
b	0.38	0.46	0.56
b1		0.46	
c	0.36	0.38	0.51
D	4.5	4.6	4.7
E	3.45	3.6	3.75
E1	1.2	1.3	1.4
e		1.27	
e1		2.54	
L	13.5	14.5	15.3
L1		1.96	
$\theta 1$		2°	
$\theta 2$		2°	
$\theta 3$		5°	

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